## Description

The HM45N02Q uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

## General Features

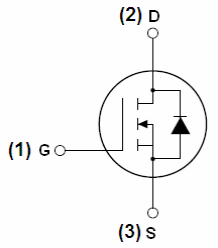
- $V_{DS}$ =20V,$I_D$ =45A
  $R_{DS(ON)}$ <5.5mΩ @ $V_{GS}$=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high $E_{AS}$
- Excellent package for good heat dissipation

## Application

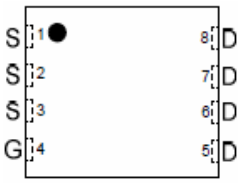
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

***100% UIS TESTED!***

***100% ΔVds TESTED!***




**Schematic diagram**




**Pin Assignment**


**DFN 3.3x3.3 EP top view**

## Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| HM45N02Q | HM45N02Q | DFN3X3-8L | - | - | - |

## Absolute Maximum Ratings ($T_C$=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 20 | V |
| Gate-Source Voltage | $V_{GS}$ | ±12 | V |
| Drain Current-Continuous | $I_D$ | 45 | A |
| Drain Current-Continuous($T_C$=100℃) | $I_D$ (100℃) | 31 | A |
| Pulsed Drain Current | $I_{DM}$ | 135 | A |
| Maximum Power Dissipation | $P_D$ | 60 | W |
| Derating factor | | 0.48 | W/℃ |
| Single pulse avalanche energy (Note 5) | $E_{AS}$ | 200 | mJ |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance,Junction-to-Case (Note 2) | $R_{\theta JC}$ | 2.1 | ℃/W |

## Electrical Characteristics ($T_C$=25℃unless otherwise noted)

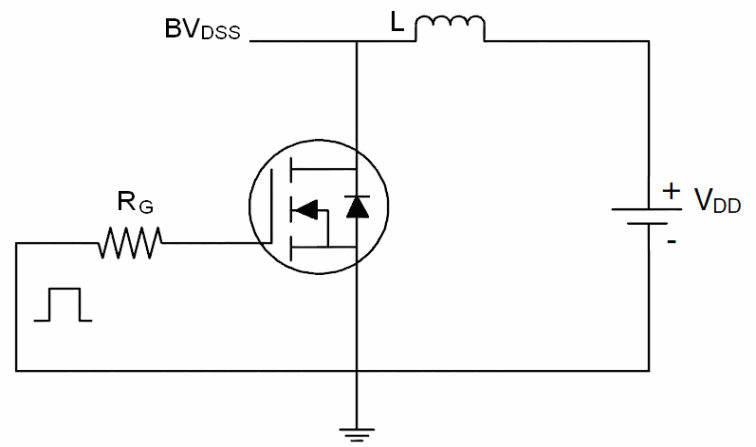
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 20 | 25 | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=20V,$V_{GS}$=0V | - | - | 1 | μA |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±12V,$V_{DS}$=0V | - | - | ±100 | nA |
| **On Characteristics** (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 0.5 | 0.7 | 1.1 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=4.5V, $I_D$=20 A | - | 3.9 | 5.5 | mΩ |
| | | $V_{GS}$=2.5V, $I_D$=15A | | 6 | 9 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=10V,$I_D$=20A | 15 | - | - | S |
| **Dynamic Characteristics** (Note4) | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=10V,$V_{GS}$=0V, F=1.0MHz | - | 2000 | - | PF |
| Output Capacitance | $C_{oss}$ | | - | 500 | - | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 200 | - | PF |
| **Switching Characteristics** (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=10V,$I_D$=2A,$R_L$=1Ω $V_{GS}$=4.5V,$R_G$=3Ω | - | 6.4 | - | nS |
| Turn-on Rise Time | $t_r$ | | - | 17.2 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 29.6 | - | nS |
| Turn-Off Fall Time | $t_f$ | | - | 16.8 | - | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=10V,$I_D$=20A, $V_{GS}$=10V | - | 27 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 6.5 | | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 6.4 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=10A | - | | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | - | - | 45 | A |
| Reverse Recovery Time | $t_{rr}$ | TJ = 25°C, IF = 20A di/dt = 100A/μs(Note3) | - | 25 | - | nS |
| Reverse Recovery Charge | Qrr | | - | 24 | - | nC |
| Forward Turn-On Time | $t_{on}$ | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

### Notes:

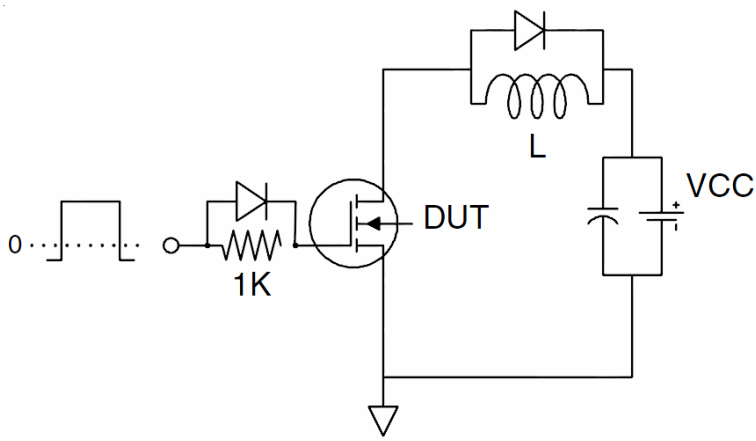
**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
**2.** Surface Mounted on FR4 Board, t ≤ 10 sec.
**3.** Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
**4.** Guaranteed by design, not subject to production
**5.** $E_{AS}$ condition : Tj=25℃,$V_{DD}$=10V,$V_G$=10V,L=0.5mH,Rg=25Ω，

## Test circuit

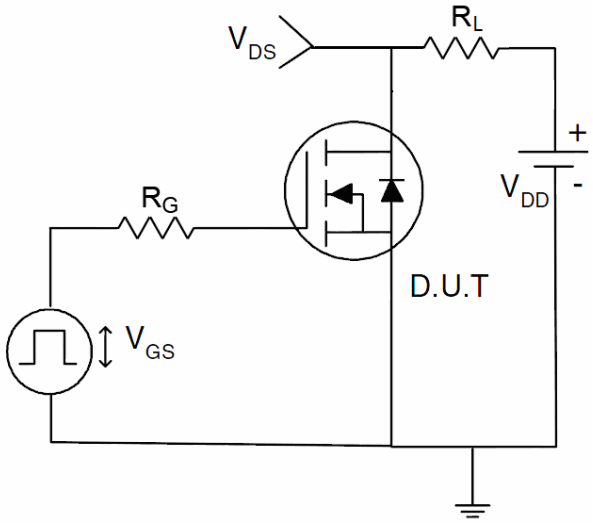
### 1) $E_{AS}$ Test Circuit




### 2) Gate Charge Test Circuit




### 3) Switch Time Test Circuit



## Typical Electrical and Thermal Characteristics (Curves)

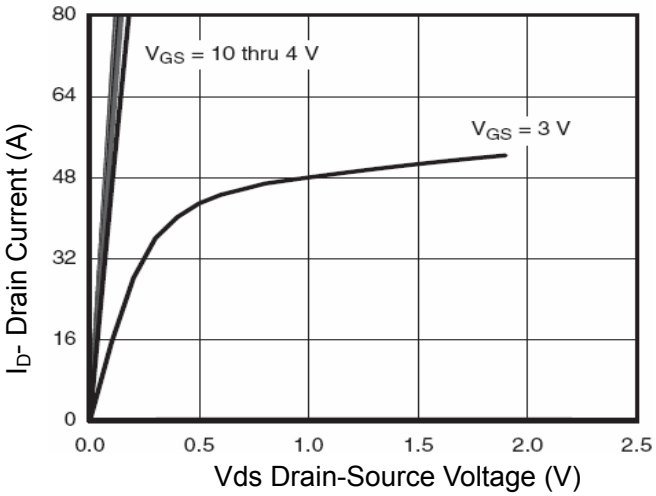



**Figure 1 Output Characteristics**

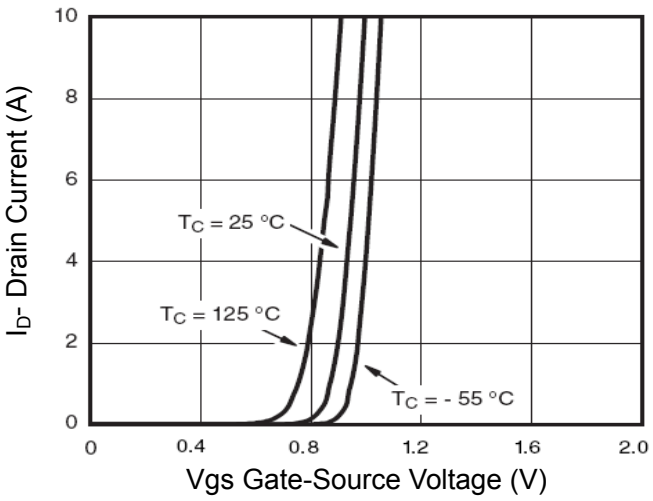



**Figure 2 Transfer Characteristics**

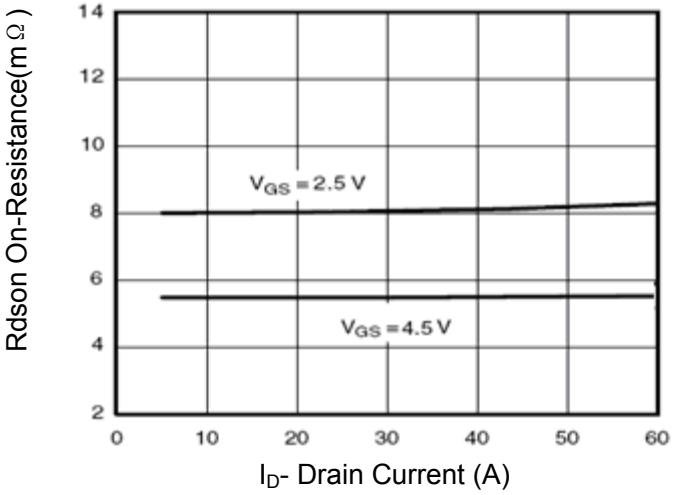



**Figure 3 Rdson- Drain Current**

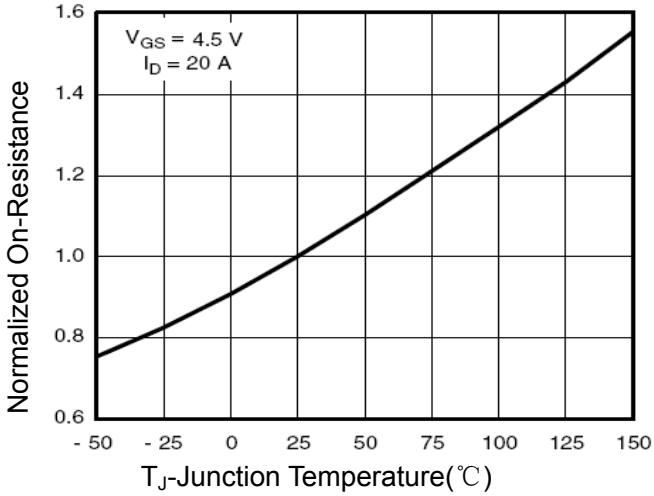



**Figure 4 Rdson-JunctionTemperature**

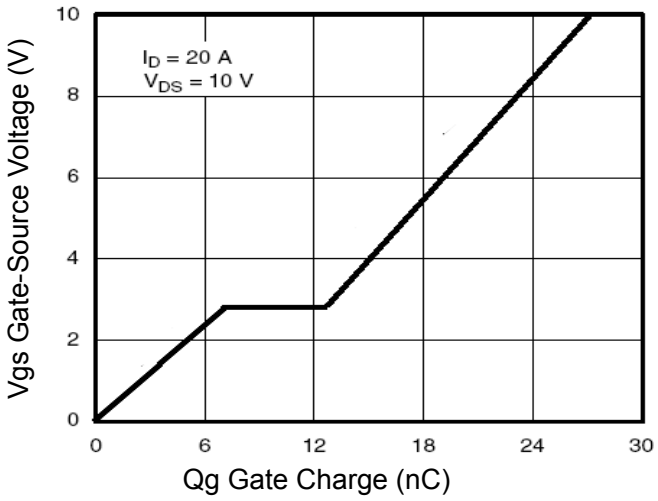



**Figure 5 Gate Charge**

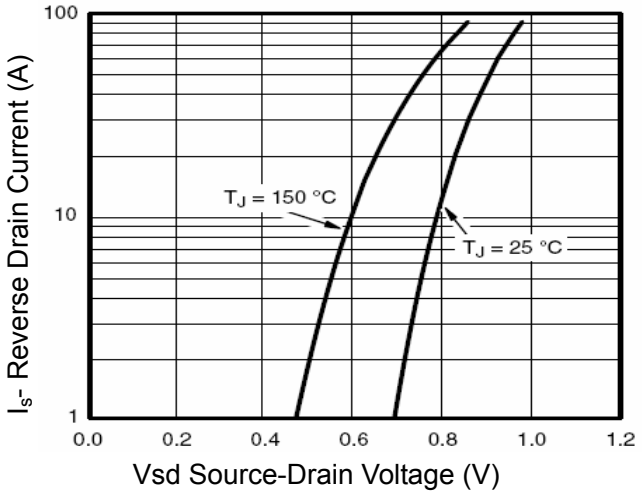



**Figure 6 Source- Drain Diode Forward**

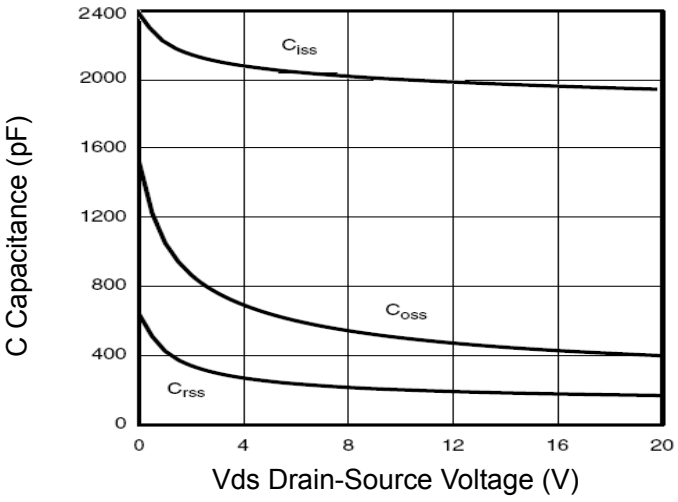



**Figure 7 Capacitance vs Vds**

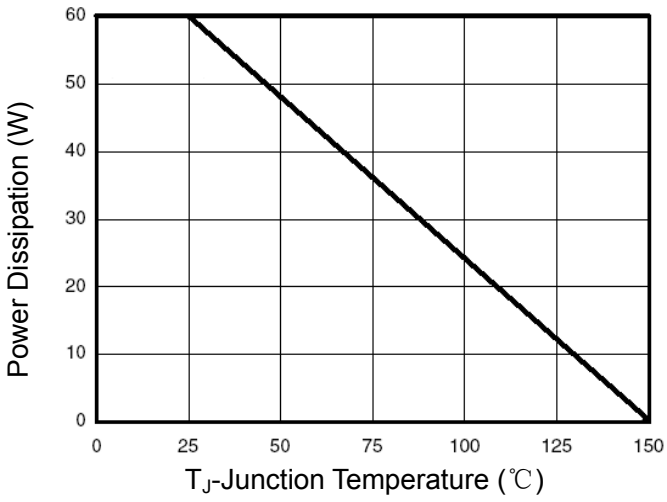



**Figure 9 Power De-rating**

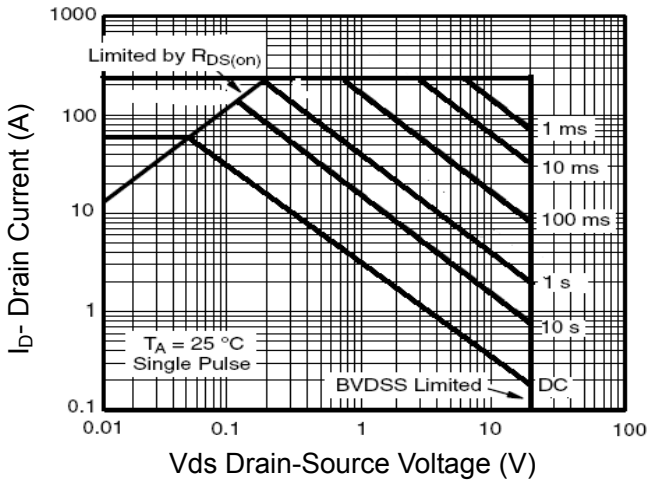



**Figure 8 Safe Operation Area**

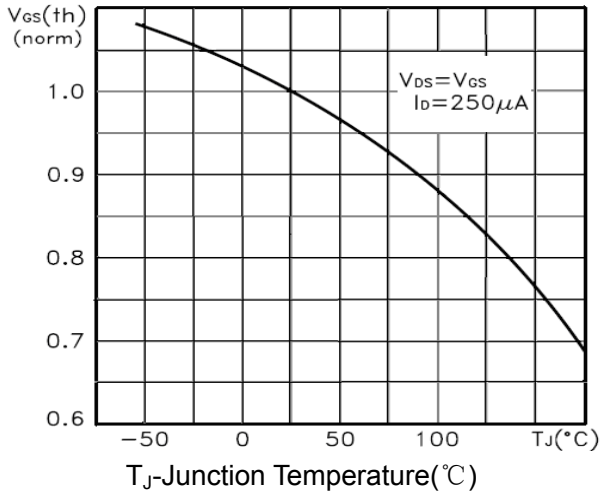



**Figure 10 $V_{GS(th)}$ vs Junction Temperature**

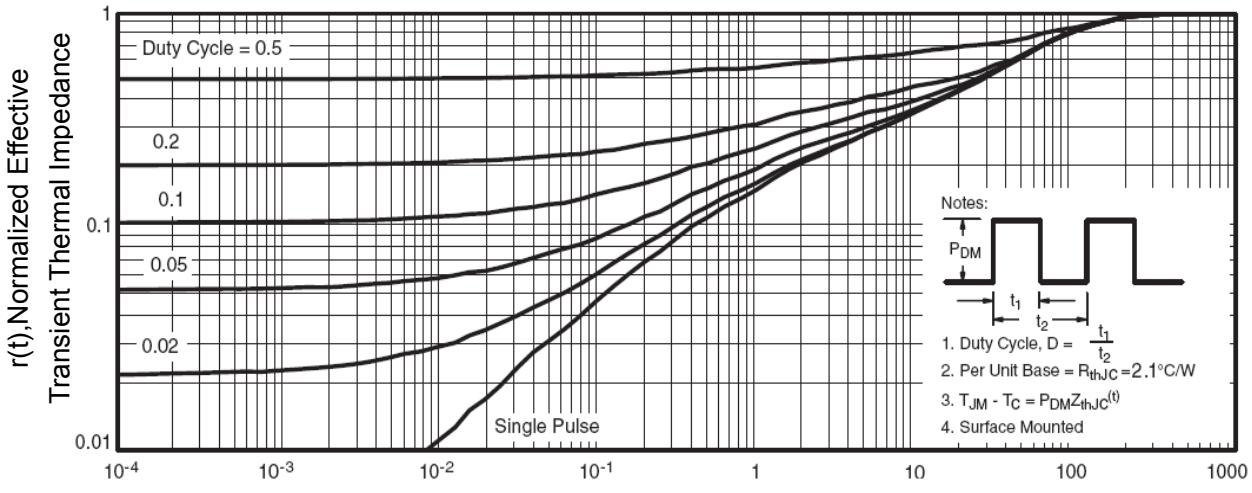
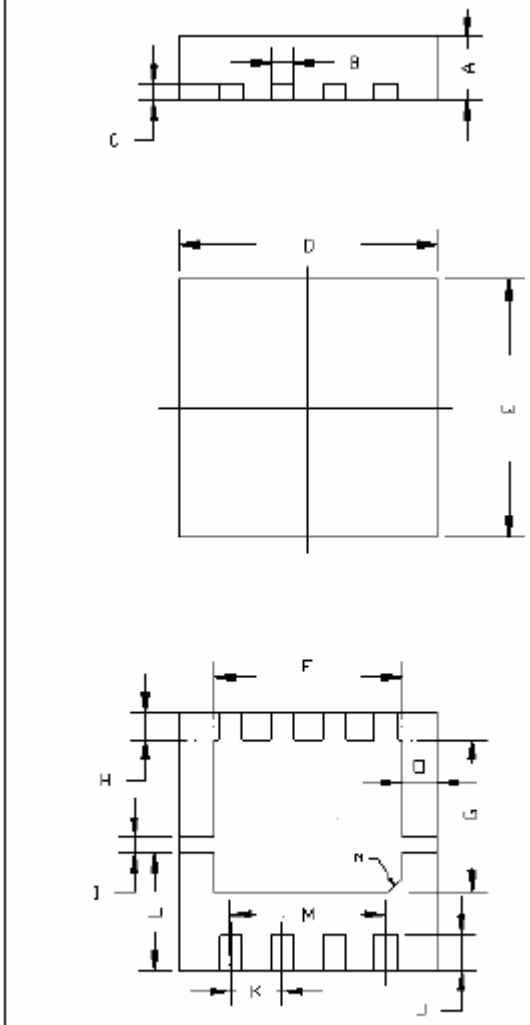



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**DFN3.3X3.3 EP Package Information**

封装外形尺寸图




| 符号 | 单位：mm | | |
|---|---|---|---|
| | MIN | MAX | TYP |
| A | 0.75 | 0.85 | 0.8 |
| B | 0.25 | 0.35 | 0.3 |
| C | 0.18 | 0.22 | 0.2 |
| D | 3.2 | 3.3 | 3.25 |
| E | 3.2 | 3.3 | 3.25 |
| F | 2.2 | 2.5 | 2.35 |
| G | 1.8 | 2.0 | 1.9 |
| H | 0.3 | 0.4 | 0.35 |
| I | 0.15 | 0.25 | 0.2 |
| J | 0.4 | 0.5 | 0.45 |
| K | 0.6 | 0.7 | 0.65 |
| L | 1.38 | 1.58 | 1.48 |
| M | 1.8 | 2.1 | 1.95 |
| N | 0.15*45° | | |
| O | 0.4 | 0.5 | 0.45 |